PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Kie Y. Ahn and Leonard Forbes Attorney Docket No.: 500466.04

Filed : Concurrently herewith

Title : FIELD EMISSION DISPLAY HAVING REDUCED POWER REQUIREMENTS AND

METHOD

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97 through 1.98, applicants wish to make known to the Patent and Trademark Office the references set forth on the attached form PTO-1449. This application relies, under 35 U.S.C. § 120, on the earlier filing dates of prior Application No. 09/994,511, filed November 26, 2001, which is a divisional application of Application No. 09/140,623, filed August 26, 1998, issuing March 23, 2004, as U.S. Patent No. 6,710,538. The references listed on the attached Form PTO-1449 were submitted to and/or cited by the Patent and Trademark Office in this prior application and, therefore, are not required to be provided in this application. If the Examiner wishes, copies will be provided upon request. Although the aforesaid references are made known to the Patent and Trademark Office in compliance with applicants' duty to disclose all information they are aware of which is believed relevant to the examination of the above-identified application, applicants believe that their invention is patentable.

Please acknowledge receipt of this Information Disclosure Statement and kindly make the cited references of record in the above-identified application.

Respectfully submitted,

DORSEY & WHITNEY LLP

Steven H. Arterberry Registration No. 46,314

Enclosure:

Form PTO-1449

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FORM PTO-1449 (REV.7-80)

EXAMINER

* EXAMINER:

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.

500466.04

APPLICATION NO.

not yet assigned

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(Use several sheets if necessary)

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FILING DATE GROUP ART UNIT

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			U.S.	PATENT DOCUMENTS			
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	3,665,241	05/23/72	Spindt et al.	313	351	,
	AB	3,755,704	08/28/73	Spindt et al.	313	309	
	AC	3,812,559	05/28/74	Spindt et al.	29	25	
	AD	3,954,523	05/04/76	Magdo et al.	438	409	
	AE	4,016,017	04/05/77	Aboaf et al.	438	441	
	AF	4,266,233	05/05/81	Bertotti et al.	257	271	
	AG	4,652,467	03/24/87	Brinker et al.	427	246	
	АН	4,857,161	08/15/89	Borel et al.	445	24	
	AI	4,987,101	01/22/91	Kaanta et al.	438	619	
	AJ	5,103,288	04/07/92	Dakamoto et al.	257	758	
	AK	5,142,184	8/25/92	Kane	313	309	
	AL	5,186,670	02/16/93	Doan et al.	445	24	
	AM	5,194,780	3/16/93	Meyer	315	169.3	
	AN	5,229,331	07/20/93	Doan et al.	437	228	
	АО	5,259,799	11/09/93	Doan et al.	445	24	
	AP	5,358,908	10/25/94	Reinbert et al.	438	20	
	AQ	5,372,973	12/13/94	Doan et al.	437	228	
	AR	5,430,300	07/04/95	Yue et al.	445	50	
	AS	5,458,518	10/17/95	Lee	445	24	
	АТ	5,470,801	11/28/95	Kapoor et al.	438	471	
	AU	5,473,222	12/05/95	Theony et al.	315	169.1	
	AV	5,483,067	01/09/96	Fujii et al.	250	338.3	
	AW	5,529,524	06/25/96	Jones	445	24	
	AX	5,569,058	10/29/96	Gnade et al.	445	24	

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Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in

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			U.S	PATENT	DOCUMENTS				
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE		NAME	CLAS	SS SUBCLASS	FILING	DATE
	AY	5,578,896	11/26/96	Huang		313	309		
	AZ	5,585,301	12/17/96	Lee et al.		437	60		
	ВА	5,597,444	01/28/97	Gilton		156	643		
	вв	5,653,619	08/05/97	Cloud et	al.	445	24		
	вс	5,663,608	09/02/97	Jones et a	1.	313	309		
	BD	5,684,356	11/04/97	Jeng et al		445	70		<u>.</u>
	ВЕ	5,712,534	1/27/98	Lee et al.		315	169.3		
	BF	5,793,154	8/11/98	Itoh et al.		313	308		
	BG	5,804,910	09/08/98	Tjaden et	al.	313	310		
	вн	5,853,492	12/29/98	Cathey et	al.	134	3		
	ві	5,869,169	02/09/99	Jones		428	213		
	ВЈ	5,898,258	04/27/99	Sakai et a	l.	313	309		
	вк	6,028,322	02/22/00	Moradi		257	10		
	BL	6,232,705	05/15/01	Forbes et	al.	313	309		
	вм	6,251,470	06/26/01	Forbes et	al.	427	97		
	BN	6,255,156	07/03/01	Forbes et	al.	438	235		
	во	6,277,765 B1	08/21/01	Cheng et	al.	438	773		
	BP	6,333,215 B1	12/25/01	Matsuda	et al.	438	149		
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		DOCUMENT NUMBER	DATE		COUNTRY	CLA	SS SUBCLASS	TRANS YES	LATION NO
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	СМ	Uh, H.S., "Process design and emission properties of gated n+ polycrystalline silicon field emitter arrafor flat-panel display applications," J. Vac. Sci. Technol. B 15(2):472-476, 1997				
	CN	Vaudaine, P. and Meyer, R., "Microtips Fluorescent Display," technical digest of IEDM 91, pp. 197-200, 1991				
	со	Zaidi, S.Z.A. et al., "Conduction Mechanisms in Co-Evaporated Mixed Mn/SioO _x Thin Films", <i>Journa of Materials Science</i> , 32:3349-3353, 1997				
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